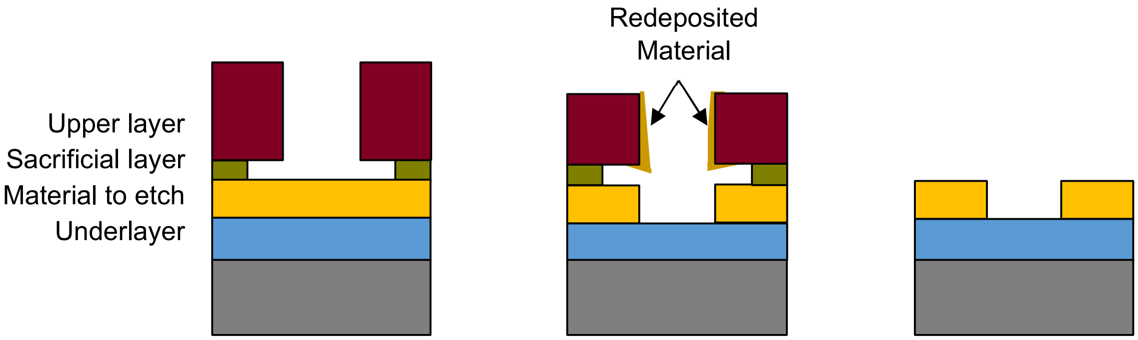

Figure 1: Process sequence showing 1) lift-off structure, b) resputtered deposition material on upper layer, c) resulting after reverse lift-off without "dog ears".

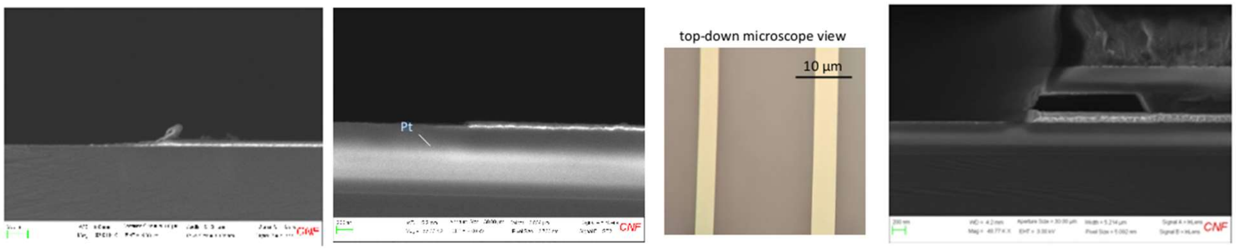

Figure 2: a) Represents 50 nm of Pt using conventional approch with single layer PR mask.removed, b) and c) show the same film using post reverse lift-off), d) shows a 150 nm Pt film without resputter sidewall features.

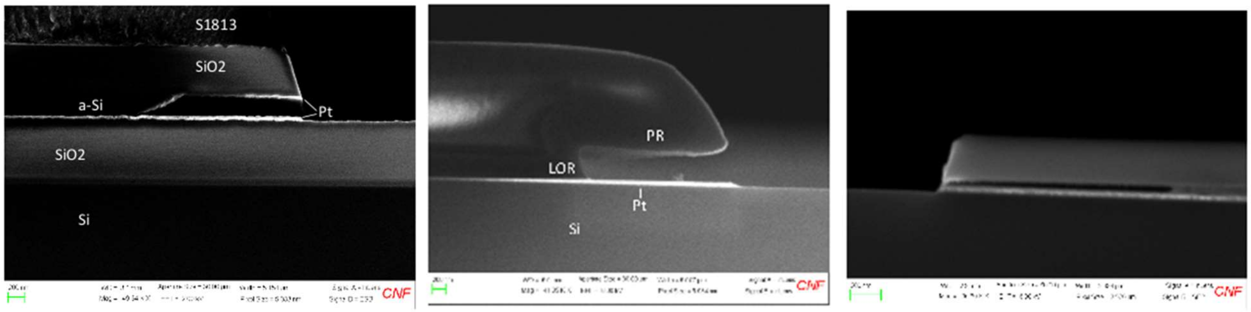

Figure 3: a) Represents 50 nm of Pt with SiO_2 as the pattern layer and a-Si as the sacrifial layer, b) using PR and LOR as the sacrificial layer, c) using PR and Cr as the sacrificial layer.